L	Hits	Search Text	IDB	Time stamp
Number				11mc Scamp
10	14147	vco	USPAT	2003/12/22
			001111	10:09
11	310	VCO and diffusion	USPAT	2003/12/22
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12	2	VCO and diffusion and "p material"	USPAT	2003/12/22
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13	1	VCO and diffusion and "p material" and	USPAT	2003/12/22
	_	CMOS	001111	10:33
14	55381	CMOS	USPAT	2003/12/22
			1	10:34
15	8	CMOS and "rectangular diffusion"	USPAT	2003/12/22
			1	10:34
16	2	CMOS and "rectangular diffusion" and	USPAT	2003/12/22
		material and well		10:34
17	2	CMOS and "rectangular diffusion" and	USPAT	2003/12/22
ı		material and well and gate		10:34
18	2	CMOS and "rectangular diffusion" and	USPAT	2003/12/22
1	}	material and well and gate and substrate		10:38
19	12246	CMOS and diffusion	USPAT	2003/12/22
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20	8246	CMOS and diffusion and material	USPAT	2003/12/22
			ì	10:38
21	7279	CMOS and diffusion and material and well	USPAT	2003/12/22
				10:38
22	6958	CMOS and diffusion and material and well	USPAT	2003/12/22
	,	and substrate	1	10:38
23	5987	CMOS and diffusion and material and well	USPAT	2003/12/22
		and substrate and gate	{	10:39
24	555	CMOS and diffusion and material and well	USPAT	2003/12/22
		and substrate and gate and polycide		10:43
25	0	CMOS and diffusion and material and well	USPAT	2003/12/22
		and substrate and gate and polycide and		10:39
	\	vco		1
26	0	CMOS and diffusion and material and well	USPAT	2003/12/22
		and substrate and gate and polycide and		10:39
		VCO		1
27	2	CMOS and diffusion and "p material" and	USPAT	2003/12/22
	L	well and substrate and gate and polycide	L	10:44